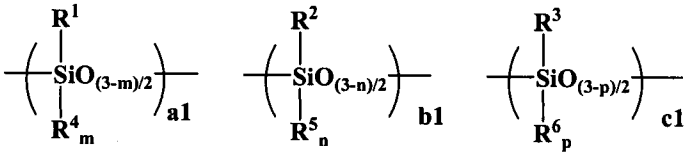
Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

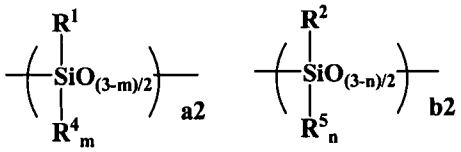
1. (Currently Amended) An anti-reflection film material used in lithography which contains at least a polymer compound having repeating units for copolymerization represented by the following general formula ~~(1).~~ (1):



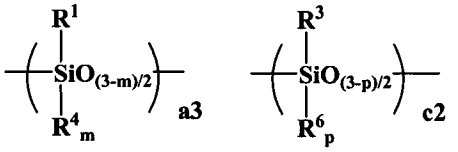
(1)

~~(In the formula,~~ wherein R^1 is a monovalent organic group having a crosslink group, R^2 is a monovalent organic group having a light-absorption group, and R^3 is a monovalent organic group which has at least one functional group selected from the group consisting of carbonyl, ester, lactone, amide, ether, and ~~nitrile.~~ nitrile; a1, b1 and c1 are $0<a1<1$, $0<b1<1$, $0<c1<1$, and ~~$0.5\leq a1+b1+c1\leq 1$. Each~~ $0.5\leq a1+b1+c1\leq 1$; each of R^4, R^5 and R^6 is a hydrogen atom, a hydroxy group, an alkyl group having 1-6 carbon atoms, an aryl group having 6-10 carbon atoms, or a fluorinated alkyl group having 1-6 carbon ~~atoms. Each~~ atoms; and each of m, n and p is 0 or 1. ~~)~~

2. (Currently Amended) An anti-reflection film material used in lithography which contains at least a polymer compound having repeating units for copolymerization represented by the following general formula (2) and a polymer compound having repeating units for copolymerization represented by the following general formula ~~(3).~~ (3):



(2)



(3)

~~(In the formula, R^1, R^2, R^3, R^4, R^5, R^6, m, n, and p are as defined above.~~ wherein R^1 is a monovalent organic group having a crosslink group, R^2 is a monovalent organic group having a light-absorption group, and R^3 is a monovalent organic group which has at least one functional group selected from the group consisting of carbonyl, ester, lactone, amide, ether, and nitrile; each of R^4, R^5, and R^6 is a hydrogen atom, a hydroxy group, an alkyl group having 1-6 carbon atoms, an aryl group having 6-10 carbon atoms, or a fluorinated alkyl group having 1-6 carbon atoms; each of m, n and p is 0 or 1; a2 and b2 are $0<a2<1$, $0<b2<1$, and ~~$0.5\leq a2+b2\leq 1$.~~ $0.5\leq a2+b2\leq 1$; and a3 and c2 are $0<a3<1$, $0<c2<1$, and $0.5\leq a3+c2\leq 1$. ~~)~~

3. (Original) The anti-reflection film material according to Claim 1 which further contains an organic solvent and/or an acid generating agent.

4. (Original) The anti-reflection film material according to Claim 2 which further contains an organic solvent and/or an acid generating agent.

5. (Original) The anti-reflection film material according to Claim 1 which further contains a crosslinking agent.

6. (Original) The anti-reflection film material according to Claim 2 which further contains a crosslinking agent.

7. (Original) The anti-reflection film material according to Claim 1 wherein the light-absorption group in the repeating unit of the polymer compound contained in the anti-reflection film material is an aromatic group or a group having a Si-Si bond.

8. (Original) The anti-reflection film material according to Claim 2 wherein the light-absorption group in the repeating unit of the polymer compound contained in the anti-reflection film material is an aromatic group or a group having a Si-Si bond.

9. (Original) A substrate which has at least an anti-reflection film obtained by baking the anti-reflection film material according to Claim 1 on the substrate.

10. (Original) A substrate which has at least an anti-reflection film obtained by baking the anti-reflection film material according to Claim 2 on the substrate.

11. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 1 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, and etching the anti-reflection film and the substrate with using as a mask the photoresist film on which the resist pattern is formed to form a pattern on the substrate.

12. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 2 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the

photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, and etching the anti-reflection film and the substrate with using as a mask the photoresist film on which the resist pattern is formed to form a pattern on the substrate.

13. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 1 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film with using as a mask the photoresist film on which the resist pattern is formed, and etching the substrate with using as a mask the anti-reflection film on which the pattern is formed, to form a pattern on the substrate.

14. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 2 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film with using as a mask the photoresist film on which the resist pattern is formed, and etching the substrate with using as a

mask the anti-reflection film on which the pattern is formed, to form a pattern on the substrate.

15. (Original) A method for forming a pattern on a substrate by lithography comprising at least, forming an organic film on the substrate, applying to the organic film the anti-reflection film material of Claim 1 and baking the anti-reflection film material to form an anti-reflection film, applying a photoresist film material to the anti-reflection film and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film using as a mask the photoresist film on which the resist pattern is formed, etching the organic film using as a mask the anti-reflection film on which the pattern is formed, and etching the substrate to form a pattern on the substrate.

16. (Original) A method for forming a pattern on a substrate by lithography comprising at least, forming an organic film on the substrate, applying to the organic film the anti-reflection film material of Claim 2 and baking the anti-reflection film material to form an anti-reflection film, applying a photoresist film material to the anti-reflection film and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film using as a mask the photoresist film on which the resist pattern is formed, etching the organic film using as a mask the anti-reflection film on which the pattern is formed, and etching the substrate to form a pattern on the substrate.